

### 30V COMPLEMENTARY MEDIUM POWER TRANSISTOR IN SOT26

### **Features**

- NPN + PNP combination
- BV<sub>CEO</sub> > 30 (-30)V
- BV<sub>CEV</sub> > 40 (-40)V
- I<sub>CM</sub> = 5 (-5)A Peak Pulse Current
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP capable (Note 4)

### Description

Advanced process capability has been used to achieve this high performance device. Combining NPN and PNP transistors in the SOT26 package provides a compact solution for the intended applications.

### **Mechanical Data**

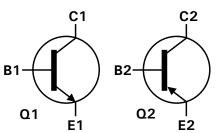
- Case: SOT26
- Case Material: molded plastic, "Green" molding compound
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208
- Weight: 0.015 grams (approximate)

### **Applications**

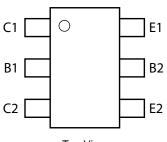
- MOSFET and IGBT gate driving
- Motor drive







Device Symbol



Top View Pin-Out

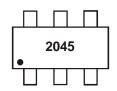
### Ordering Information (Notes 4 & 5)

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTC2045E6TA	AEC-Q101	2045	7	8	3,000
ZXTC2045E6QTA	Automotive	2045	7	8	3,000

### Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/ for more information about Diodes Incorporated's definitions of Halogen and Antimony free, "Green" and Lead-Free.
- 3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- Automotive products are AEC-Q101 qualified and PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified.
- 5. For packaging details, go to our website at http://www.diodes.com

## **Marking Information**



2045 = Product Type Marking Code



## Maximum Ratings – Q1 (NPN Transistor) (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	$V_{CBO}$	40	V
Collector-Emitter Voltage	$V_{CEV}$	40	V
Collector-Emitter Voltage	$V_{CEO}$	30	V
Emitter-Base Voltage	V <sub>EBO</sub>	7	V
Continuous Collector Current	Ic	1.5	Α
Peak Pulsed Collector Current	Ісм	5	Α
Base Current	Ι <sub>Β</sub>	1	Α

## Maximum Ratings - Q2 (PNP Transistor) (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	$V_{CBO}$	-40	V
Collector-Emitter Voltage	V <sub>CEV</sub>	-40	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-30	V
Emitter-Base Voltage	V <sub>EBO</sub>	-7	V
Continuous Collector Current	I <sub>C</sub>	-1.5	Α
Peak Pulsed Collector Current	I <sub>CM</sub>	-5	Α
Base Current	l <sub>Β</sub>	-1	А

## Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

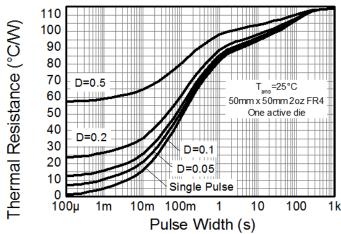
Characteristic	Symbol	Value	Unit		
	(Notes 6 & 10)		0.7 5.6		
	(Notes 7 & 10)		0.9 7.2	W mW/°C	
Power Dissipation Linear Derating Factor	(Notes 7 & 11)	$P_{D}$	1.1 8.8		
-	(Notes 8 & 10)		1.1 8.8		
	(Notes 9 & 10)	1	1.7 13.6		
	(Notes 6 & 10)		179		
	(Notes 7 & 10)		139	2000	
Thermal Resistance, Junction to Ambient	(Notes 7 & 11)	$R_{\theta JA}$	113		
	(Notes 8 & 10)		113	°C/W	
	(Notes 9 & 10)		73		
Thermal Resistance, Junction to Lead	(Note 12)	$R_{ heta JL}$	95.50		
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C		

Notes:

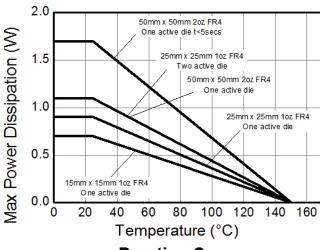
- 6. For a device surface mounted on 15mm x 15mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
- 7. Same as note (6), except the device is surface mounted on 25mm x 25mm 1oz copper.
- 8. Same as note (6), except the device is surface mounted on 50mm x 50mm 2oz copper.
- 9. Same as note (8), except the device is measured at t < 5 seconds.
- 10. For device with one active die, both collectors attached to a common heatsink.
- 11. For device with two active dice running at equal power, split heatsink 50% to each collector.
- 12. Thermal resistance from junction to solder-point (at the end of the collector lead).



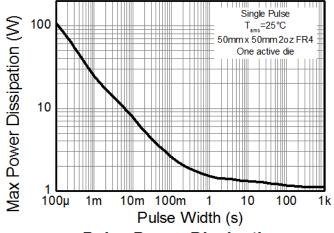
### **Thermal Characteristics and Derating Information**



**Transient Thermal Impedance** 



**Derating Curve** 



**Pulse Power Dissipation** 





# Electrical Characteristics – Q1 (NPN Transistor) (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS							
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	40	-	_	V	$I_C = 100 \mu A, I_E = 0$	
Collector-Emitter Breakdown Voltage	$BV_{CEV}$	40	-		V	$I_C = 1\mu A$ , $0.25V > V_{BE} > 1.0V$	
Collector-Emitter Breakdown Voltage (Note 13)	BV <sub>CEO</sub>	30	-	_	V	$I_C = 10 \text{mA}, I_B = 0$	
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	7	8.3		V	$I_E = 100 \mu A, I_C = 0$	
Collector Cutoff Current	I <sub>CBO</sub>	_	<1	20	nA	V <sub>CB</sub> = 32V	
Collector Cutoff Current	I <sub>CES/R</sub>	_	<1	20	nA	$V_{CE} = 16V, R \le 1k\Omega$	
Emitter Cutoff Current	I <sub>EBO</sub>	_	<1	20	nA	V <sub>EB</sub> = 6V	
ON CHARACTERISTICS (Note 13)							
DC Current Gain	h <sub>FE</sub>	180	300	500		$I_C = 100 \text{mA}, V_{CE} = 2 \text{V}$	
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>			375	mV	$I_C = 750 \text{mA}, I_B = 15 \text{mA}$	
Base-Emitter Saturation Voltage	$V_{BE(sat)}$			1200	mV	$I_C = 750 \text{mA}, I_B = 15 \text{mA}$	
SMALL SIGNAL CHARACTERISTICS							
Output Capacitance	$C_{obo}$		9	20	pF	V <sub>CB</sub> = 10V, f = 1.0MHz	
Current Gain-Bandwidth Product	$f_T$		265		MHz	$V_{CE} = 10V, I_{C} = 50mA, f = 100MHz$	
Delay Time	t <sub>d</sub>		10		ns		
Rise Time	t <sub>r</sub>		12		ns	$V_{CC} = 10V, I_{C} = 1A$	
Storage Time	ts		185		ns	$I_{B1} = -I_{B2} = 50 \text{mA}$	
Fall Time	t <sub>f</sub>	_	45	_	ns		

# Electrical Characteristics – Q2 (PNP Transistor) (@TA = +25°C, unless otherwise specified.)

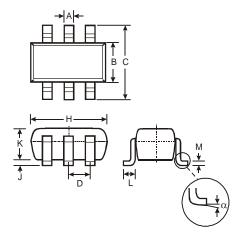
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	$BV_{CBO}$	-40	-		V	$I_C = -100 \mu A, I_E = 0$
Collector-Emitter Breakdown Voltage	$BV_CEV$	-40	-		V	$I_C = -1\mu A$ , $0.25V < V_{BE} < 1.0V$
Collector-Emitter Breakdown Voltage (Note 13)	BV <sub>CEO</sub>	-30	-		V	$I_C = -10 \text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	$BV_{EBO}$	-7	-8.3	_	V	$I_E = -100 \mu A, I_C = 0$
Collector Cutoff Current	I <sub>CBO</sub>	_	<-1	-20	nA	V <sub>CB</sub> = -32V
Collector Cutoff Current	I <sub>CES/R</sub>	_	<-1	-20	nA	$V_{CE}$ = -16V, R $\leq$ 1k $\Omega$
Emitter Cutoff Current	I <sub>EBO</sub>	_	<-1	-20	nA	V <sub>EB</sub> = -6V
ON CHARACTERISTICS (Note 13)						
DC Current Gain	$h_{FE}$	180	300	500	_	$I_C = -100 \text{mA}, V_{CE} = -2 \text{V}$
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>			-375	mV	$I_C = -750 \text{mA}, I_B = -15 \text{mA}$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$			-1200	mV	$I_C = -750 \text{mA}, I_B = -15 \text{mA}$
SMALL SIGNAL CHARACTERISTICS						
Output Capacitance	$C_{obo}$		9	20	рF	V <sub>CB</sub> = -10V, f = 1.0MHz
Current Gain-Bandwidth Product	$f_T$		195		MHz	$V_{CE} = -10V$ , $I_{C} = -50mA$ , $f = 100MHz$
Delay Time	t <sub>d</sub>		16		ns	
Rise Time	t <sub>r</sub>		11	_	ns	$V_{CC} = -10V, I_{C} = -1A$
Storage Time	ts		220		ns	$I_{B1} = -I_{B2} = -50 \text{mA}$
Fall Time	t <sub>f</sub>	_	31	_	ns	

Notes: 13. Measured under pulsed conditions. Pulse width  $\leq 300 \mu s.$  Duty cycle  $\leq 2\%.$ 



# **Package Outline Dimensions**

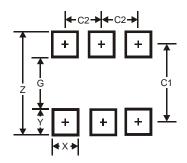
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SOT26						
Dim	Min	Max	Тур			
Α	0.35	0.50	0.38			
В	1.50	1.70	1.60			
ပ	2.70	3.00	2.80			
D	_		0.95			
H	2.90	3.10	3.00			
۲	0.013	0.10	0.05			
K	1.00	1.30	1.10			
L	0.35	0.55	0.40			
M	0.10	0.20	0.15			
α	0°	8°	_			
All Dimensions in mm						

# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	3.20
G	1.60
Х	0.55
Y	0.80
C1	2.40
C2	0.95





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